

**Listing of Claims:**

1. (Currently Amended) A semiconductor device, comprising:  
a substrate;  
a ~~[[one]]~~ conductive type semiconductor layer provided on the substrate and having a sectorial or trapezoidal shape ~~of which~~ including an opening angle ~~[[is]] of at least 20 degrees or more;~~ and  
a transistor provided on the ~~[[one]]~~ conductive type semiconductor layer such that electric current flows along a grain boundary.
2. (Currently Amended) A thin film transistor, comprising:  
a ~~[[one]]~~ conductive type semiconductor layer;  
a source region and a drain region ~~[[which]]~~ that are separately provided in the semiconductor layer such that electric current flows along a grain boundary;  
~~[[and]]~~  
a gate electrode provided above or below the semiconductor layer with an insulating film interposed therebetween~~[[,]]; and~~  
wherein ~~the width of the~~ a channel region is located between the source region and the drain region and a first junction face extends between the source region and ~~[[a]] the channel region that is provided between the source region and the drain region, is different and has a first junction face width, and a second junction face extends between the channel region and the drain region and has a second junction face width, and wherein the first junction face width differs from the second junction face width of the junction face between the channel region and the drain region.~~
3. (Currently Amended) A thin film transistor as claimed in claim 2, wherein ~~[[said]] the semiconductor layer has an approximately trapezoid a trapezoidal or approximately sector plane shape.~~
4. (Currently Amended) A thin film transistor as claimed in claim 3, wherein ~~said trapezoid~~ the trapezoidal or sector plane shape has an opening angle of at least 20 degrees or more.
5. (Currently Amended) A thin film transistor as claimed in ~~any one of claims 2 through 4~~ claim 2, wherein ~~[[said]] the semiconductor layer includes one or more grain boundaries, which extend each of which extends in the direction one of the following two directions: (1) from the source region to the drain region~~ one of the following two directions: (1) from the source region to the drain region ~~[[or]] and (2) from the drain region to the source region of the semiconductor layer.~~

6. (Currently Amended) A thin film transistor as claimed in claim 3 ~~[[or 4]]~~, wherein ~~[[said]]~~ the semiconductor layer includes two or more grain boundaries, each of which extends in ~~the direction~~ one of the following two directions: (1) from the source region to the drain region ~~[[or]]~~ and (2) from the drain region to the source region of the semiconductor layer, and ~~[[also,]]~~ each of which extends in the in-plane ~~direction of~~ with the semiconductor layer in correspondence with ~~[[the]]~~ an opening angle of the trapezoid trapezoidal or sector plane shape.

7. (Currently Amended) A thin film transistor as claimed in claim 2, wherein ~~[[said]]~~ the semiconductor layer includes at least two or more grain boundaries, each of which extends in ~~the direction~~ one of the following two directions: (1) from the source region to the drain region ~~[[or]]~~ and (2) from the drain region to the source region of the semiconductor layer, and ~~[[also,]]~~ wherein at least two of the grain boundaries are adjacent to each other and extend in the in-plane ~~with direction of~~ the semiconductor layer in correspondence with an opening angle.

8. (Currently Amended) A thin film transistor as claimed in claim 2, wherein ~~[[said]]~~ the semiconductor layer includes at least two ~~[[or more]]~~ crystal grain boundaries, each of which extends in ~~the direction~~ one of the following two directions: (1) from the source region to the drain region ~~[[or]]~~ and (2) from the drain region to the source region of the semiconductor layer, ~~and also, the~~ semiconductor layer further including two grain boundaries adjacent to each other ~~[[are]]~~ and in parallel with ~~[[the]]~~ an in-plane direction of the semiconductor layer.

9. (Currently Amended) A thin film transistor as claimed in ~~any one of claims 5 through 8,~~ wherein ~~the difference between two angles is 20 degrees or more, one of said two angles being an~~ claim 5, further including a first angle ~~[[made]]~~ formed by ~~[[one]]~~ (1) an imaginary line connecting the middle position of the first junction face ~~width of the junction face between the channel region and the source region with the middle position of the width of the junction face between the channel region and the drain region and the other~~ and (2) an imaginary line connecting the middle of the second junction face width ~~extending in the extending direction of the grain boundary,~~ and the other a second angle being an opening angle defined by the first junction face ~~width of the junction face between the channel region and the source region and the~~ second junction face

~~width of the junction face between the channel region and the drain region,~~  
wherein the difference between the two angles is at least 20 degrees.

10. (Currently Amended) A circuit apparatus<sub>1</sub> comprising:

a substrate;

a thin film transistor as recited in ~~any one of claims 2 through 9~~ claim 2 and formed directly or indirectly on the substrate, the thin film transistor being of N-type; ~~[[and]]~~

a thin film transistor as recited in ~~any one of claims 2 through 9~~ claim 2 and formed directly or indirectly on the substrate, the thin film transistor being of P-type~~[[,]]~~; and

wherein the thin film transistor of N-type and the thin film transistor of P-type are arranged to take point-symmetrical positions, respectively.

11. (Currently Amended) A liquid crystal display<sub>1</sub> comprising:

a thin film transistor as recited in ~~any one of claims 2 through 9~~ claim 2.

12. (Currently Amended) A liquid crystal display<sub>1</sub> comprising:

a circuit apparatus as recited in claim 10.

13. (Currently Amended) A circuit apparatus<sub>1</sub> comprising~~[[,]]~~:

a substrate;

a semiconductor film having ~~a lot of~~ multiple grain boundaries and provided on the substrate; and

a thin film transistor ~~[[which]]~~ that is formed in the semiconductor film~~[[,]]~~ and in which electric current flows in parallel with ~~[[the]]~~ a direction of one of the grain boundaries.

14. (Currently Amended) A circuit apparatus<sub>1</sub> comprising~~[[,]]~~:

a substrate;

a semiconductor film provided on the substrate and having ~~a lot of~~ multiple grain boundaries; and

a plurality of thin film transistors ~~[[which]]~~ that are formed in a directional plane that is the same as a directional ~~plane direction~~ of the semiconductor film~~[[,]]~~ and in which an electric current flows in parallel with the direction of each of the grain boundaries.